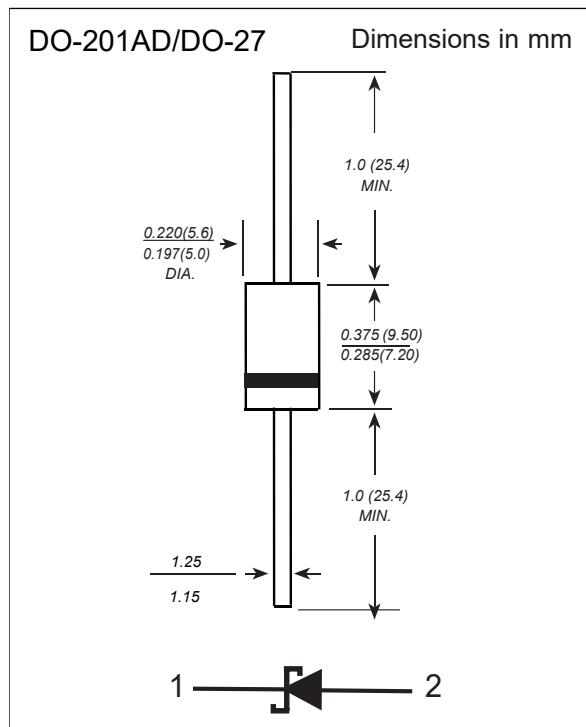


■ Features

- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds, 0.375" (9.5mm) lead length, 5
- Comply with RoHS standard

■ Mechanical Data

- package: DO-201AD/DO-27
- Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any



■ Maximum Ratings And Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	SYMBOLS	1N5820	1N5821	1N5822	UNITS
Maximum repetitive peak reverse voltage	V _{RMM}	20	30	40	V
Maximum RMS voltage	V _{RMS}	14	21	28	V
Maximum DC blocking voltage	V _{DC}	20	30	40	V
Maximum average forward rectified current 0.375”(9.5mm) lead length(see fig.1)	I _(AV)	3.0			A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	80.0			A
Maximum instantaneous forward voltage at 10.0A	V _F	0.50	0.55		V
Maximum DC reverse current at rated DC blocking voltage T _A =25℃ T _A =100℃	I _R	0.3			mA
		15.0			
Typical junction capacitance (NOTE 1)	C _J	150			pF
Typical thermal resistance (NOTE 2)	R _{θJA}	40.0			℃/W
Operating junction and storage	T _J	-65 to +125			℃
Storage temperature range	T _{STG}	-65 to +125			℃



■ Characteristics Curves($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Fig. 1- Forward Current Derating Curve

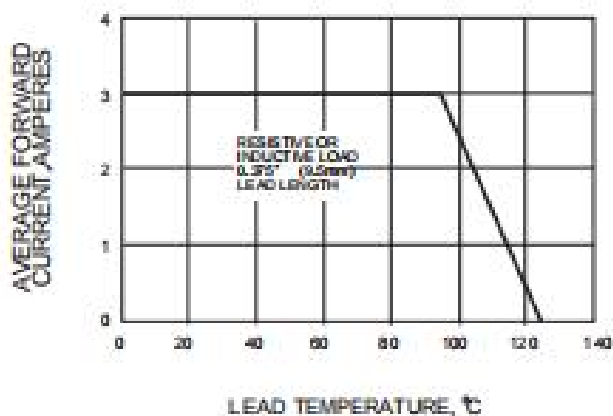


Fig. 2-Maximum Non-Repetitive Peak Forward Surge Current

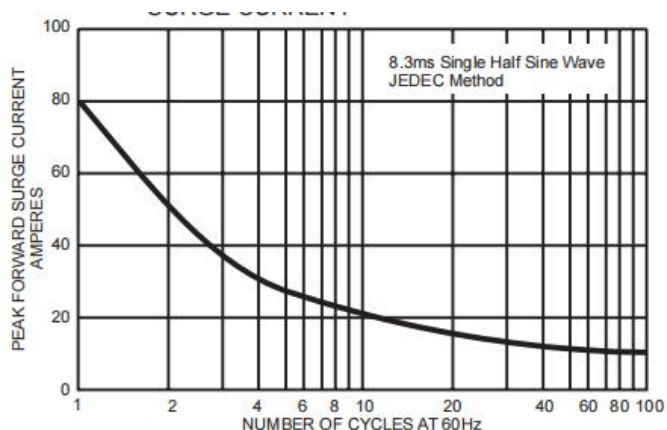


Fig. 3-Typical Reverse Characteristics

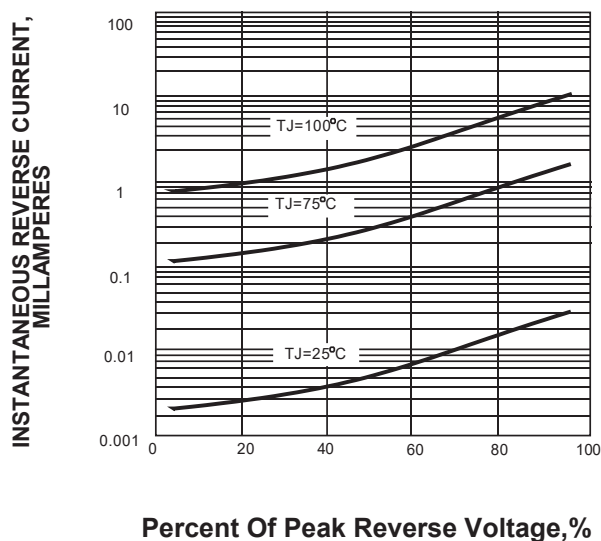


Fig. 4-Typical Transient Thermal Impedance

